

GaAs PIN PHOTODIODES

PD-8150 Series

PIN Photodiode with Mini-Size TO Package

FEATURES

- ✧ High Responsivity for 850 nm
- ✧ Low Dark Current
- ✧ Quick Pulse Response
- ✧ 2.4 mm Mini-Size Package
- ✧ Active Diameter 100 μ m

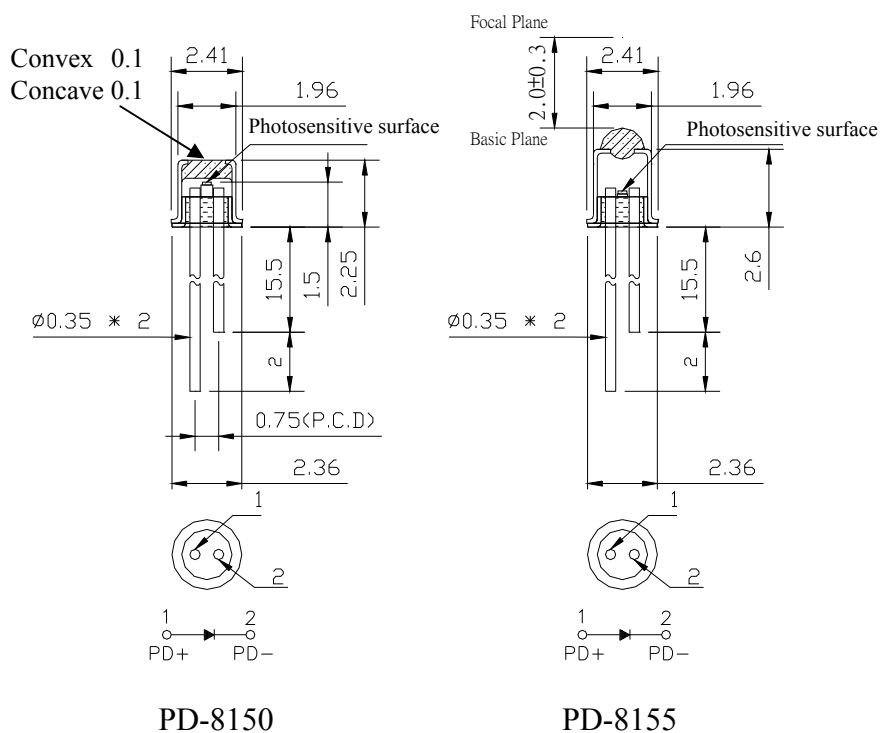
DESCRIPTION

PD-8150 series InGaAs Photodiode are suited to receive the light at the wavelength range from 600 nm to 1000 nm. With high reliability, PD-8150 series are the best choice for datacom application.

ELECTRICAL AND OPTICAL CHARACTERISTICS (T _C =25°C)						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			100		μ m
	Detection Range		600		1000	nm
R	Responsivity	V _R =5V, λ =850nm	0.45	0.5	-	A/W
I _{dark}	Dark Current	V _R =5V		0.1	0.7	nA
C	Capacitance	V _R =5V		0.4	0.7	pF
T _r /T _f	Rise/Fall Time	V _R =5V, 10~90%			0.15	ns
BW	Bandwidth	V _R =5V	2			GHz

ABSOLUTE MAXIMUM RATINGS (T _C =25 °C)			
Symbol	Parameter	Ratings	Unit
P _o	Input Optical Power	10	mW
V _{RD}	Reverse Voltage	20	V
I _{FD}	Forward Current	10	mA
T _{opr}	Operating Temperature	-40~+85	°C
T _{stg}	Storage Temperature	-40~+85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



ORDER INFORMATION

Part No.: P D - 8 1 5 ☐ - ☐ ☐ ☐

Code	Cap
0	Flat Window
5	Ball lens

Code	Chip Diameter
100	100 μ m

Revision History

Version	Subject	Release Date
1.0	Initial datasheet	2004/8/1
2.0	Revise mechanical drawing	2009/4/9
